

# MG1A01 GaAs Hall

#### MG1A01砷化镓霍尔元件

• Linear GaAs Hall Element

#### 线性砷化镓霍尔元件

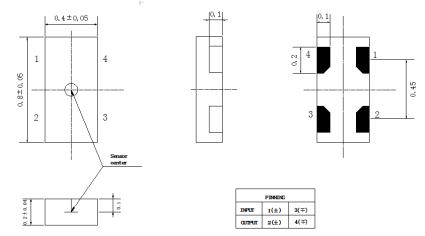
• Excellent Thermal Characteristics

#### 卓越的热稳定特性

• Thin-type DFN Package

#### 超薄 DFN 封装

#### • 外形尺寸图 Dimensional Drawing (Unit MM)



Sensing center diameter  $\Phi = 0.3$  mm

## ● 最大额定值 Absolute Maximum Rating

Operating Temperature Range  $-40^{\circ}$ C ~ 125°C 工作温度 Storage Temperature Range  $-40^{\circ}$ C ~ 150°C 存储温度 Maximum Input Voltage  $V_c$  [V] 9.5V 最大输入电压 $V_c$  [V] Maximum Input Power  $P_0$  [mW] 105mW 最大输入功率

## ● 电气特性 (室温 25℃) Electrical Characteristics (RT=25℃)



Table 1. Electrical Characteristics of MG1A01.

	-		-			
项目 Item	符号 Symbol	<b>测量条件</b> Test Condi.	最小 Min.	标准 Typ.	最大 Max.	<b>单位</b> Unit
霍尔电压 Hall Voltage	<b>V</b> H	$\boldsymbol{B}$ = 50mT, V <sub>c</sub> =6V $\boldsymbol{T}_{a}$ = RT	55		75	mV
输入电阻 Input Resistance	<b>R</b> <sub>in</sub>	$\boldsymbol{B}$ = 0mT, $\boldsymbol{I}_{c}$ = 0.1mA $\boldsymbol{T}_{a}$ = RT	650		850	Ω
输出电阻 Output Resistance	<b>R</b> out	$\boldsymbol{B}$ = 0mT, $\boldsymbol{I}_{c}$ = 0.1mA $\boldsymbol{T}_{a}$ = RT	650		850	Ω
<b>非平衡电压</b> Offset Voltage	V <sub>os</sub>	$\boldsymbol{B}$ = 0mT, V <sub>C</sub> = 6V $\boldsymbol{T}_{a}$ = RT	-5		+5	mV
输出电压温度系数 Temp. Coeffi. of И <sub>н</sub>	α <b>V</b> _	<b>B</b> = 50mT, <b>I</b> <sub>C</sub> =5mA, <b>T</b> <sub>a</sub> = 25°C ~ 125°C			0.06	%/°C
输入电阻温度系数 Temp. Coeffi. of <b>R</b> in	$lpha \pmb{R}_{ m in}$	<b>B</b> = 0mT, <b>I</b> <sub>C</sub> =0.1mA, <b>T</b> <sub>a</sub> = 25°C ~ 125°C			0.3	%/°C
线性度 linearity	$\Delta K$	<b>B</b> = 0.1 ~ 0.5T, <b>I</b> <sub>C</sub> =5mA, <b>T</b> <sub>a</sub> = RT	-2		2	%

#### 表 1. MG1A01 电气特性

Note:

 $1. \quad \boldsymbol{V}_{\mathrm{H}} = \boldsymbol{V}_{\mathrm{H}-\mathrm{M}} - \boldsymbol{V}_{\mathrm{os}}$ 

in which  $V_{H-M}$  is the Output Hall Voltage,  $V_H$  is the Hall Voltage and  $V_{os}$  is the offset Voltage under the identical electrical stimuli.

2. 
$$\alpha V_{\rm H} = \frac{1}{V_{\rm H} (T_{a1})} \times \frac{V_{\rm H} (T_{a2}) - V_{\rm H} (T_{a1})}{T_{a2} - T_{a1}} \times 100$$
  
 $T_{a1} = 25^{\circ}\text{C}, \quad T_{a2} = 125^{\circ}\text{C}$   
3.  $\alpha R_{\rm in} = \frac{1}{R_{\rm in} (T_{a1})} \times \frac{R_{\rm in} (T_{a2}) - R_{\rm in} (T_{a1})}{T_{a2} - T_{a1}} \times 100$ 

$$T_{a1} = 25^{\circ}\text{C}, \quad T_{a2} = 125^{\circ}\text{C}$$

4. 
$$\Delta \mathbf{K} = \frac{\mathbf{K}(\mathbf{B}_1) - \mathbf{K}(\mathbf{B}_2)}{\frac{\mathbf{K}(\mathbf{B}_1) + \mathbf{K}(\mathbf{B}_2)}{2}} \times 100 \qquad \mathbf{K} = \frac{\mathbf{V}_{\mathrm{H}}}{\mathbf{I}_c \times \mathbf{B}}$$



## ● 特征曲线图 Characteristic Curves

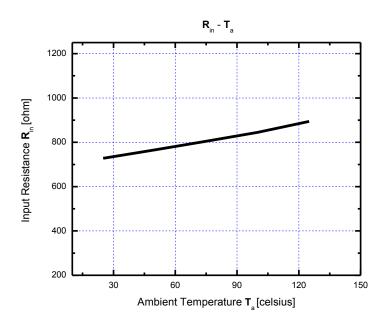


Figure 1. Input resistance  $R_{in}$  as a function of ambient temperature  $T_{a}$ .



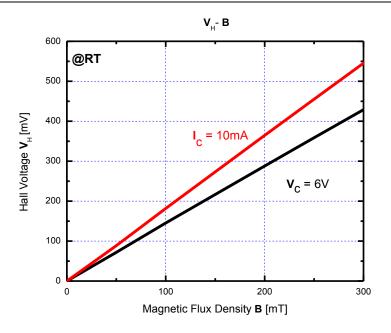


Figure 2. Hall voltage  $V_{H}$  as a function of magnetic flux density **B**.

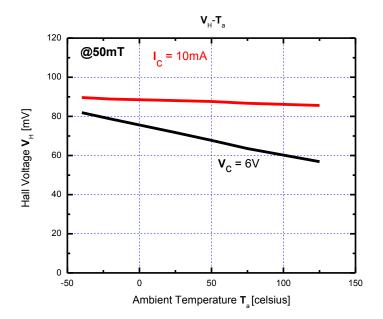


Figure 3. Hall voltage  $V_{\text{H}}$  as a function of ambient temperature  $T_{\text{a.}}$ 



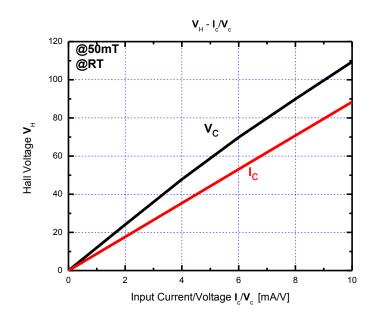


Figure 4. Hall voltage  $V_{\rm H}$  as a function of electrical stimuli  $I_{\rm c}/V_{\rm c}$ .



#### ● ESD 预防措施

本产品是对ESD(静电放电)敏感的设备。在以下环境中处理带有ESD警告标记的霍尔元件:

- 不太可能出现静电荷的环境 (例如:相对湿度超过40%RH)。

- 处理器件时佩戴防静电服和腕带

- 对于直接接触器件的容器建议实施ESD防护措施。

#### ● 存储注意事项

- 在开封MBB后,产品应在适当的温度和湿度(5至35℃,40至60%RH)下储存。强烈建议使用自密封

- 袋,使产品远离氯气和腐蚀性气体。
- 长期储存

产品用MBB密封

-对于超过2年的储存,建议在MBB密封的氮气氛中储存。大气中的水氧会导致器件引脚氧化,从而导致

引脚焊接能力变差。

## ● 安全注意事项

-不要通过燃烧,粉碎或化学处理等方式将本产品变成气体,粉末或液体。

-丢弃本产品时,请遵守法律和公司规定。



#### • Precautions for ESD

This product is the device that is sensitive to ESD (Electrostatic Discharge). Handling Hall Elements with the ESD-Caution mark under the environment in which

- Static electrical charge is unlikely to arise. (Ex; Relative Humidity; over 40%RH).
- Wearing the antistatic suit and wristband when handling the devices.
- Implementing measures against ESD as for containers that directly touch the devices.

#### • Precautions for Storage

- Products should be stored at an appropriate temperature and humidity (5 to 35°C, 40 to 60%RH) after the unsealing of MBB. Keeping products away from chlorine and corrosive gas.

#### - Long-term storage

Products are sealed in MBB.

- For storage longer than 2 years, it is recommended to store in nitrogen atmosphere with MBB sealed.

Oxygen and H<sub>2</sub>O of atmosphere oxidizes leads of products and lead solder ability get worse.

#### • Precautions for Safety

- Do not alter the form of this product into a gas, powder or liquid through burning, crushing or chemical processing.

- Observe laws and company regulations when discarding this product.

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